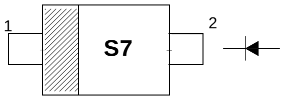
Plastic-Encapsulate Diodes

Schottky Barrier Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "**S7** "
Simplified outline SOD-123 and symbol

FEATURES

- Small power mold type.
- Low IR
- High reliability.
- Silicon epitaxial planar

Marking: S7

MAXIMUM RATINGS(Ta = 25ºC)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	VRM	40	V
Reverse voltage (DC)	VR	40	V
Average rectified forward current	IO	1	A
Forward current surge peak (60Hz・1cyc)	IFSM	5.5	A
Junction temperature	TJ	150	℃
Storage temperature range	TSTG	–40 ~ +150	℃

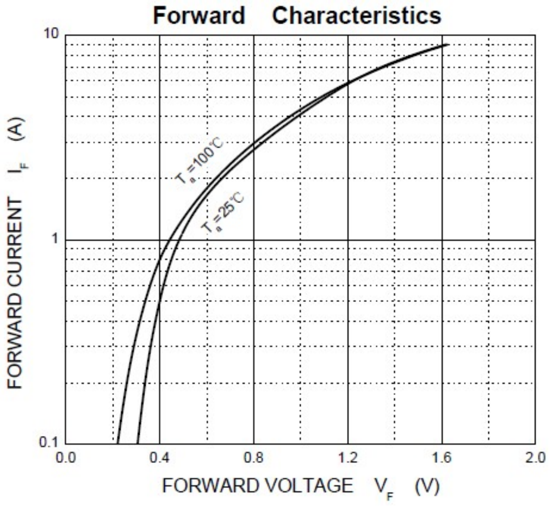
THERMAL CHARACTERISTICS

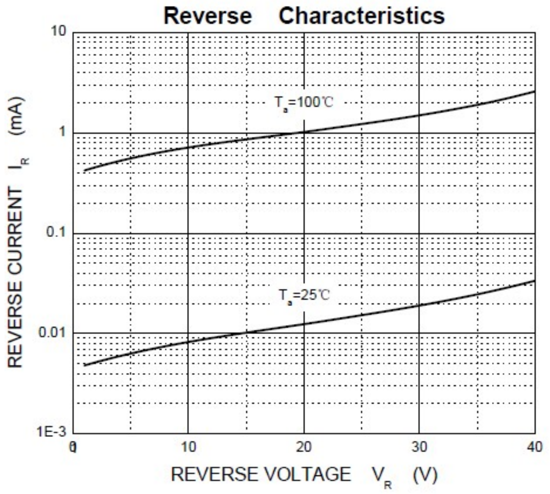
Parameter	Symbol	Limits	Unit
Power Dissipation	PD	400	mW
Thermal Resistance,Junction–to–Ambient	RΘJA	312	ºC/W
Thermal Resistance,Junction–to–Case	RΘJC	150	ºC/W

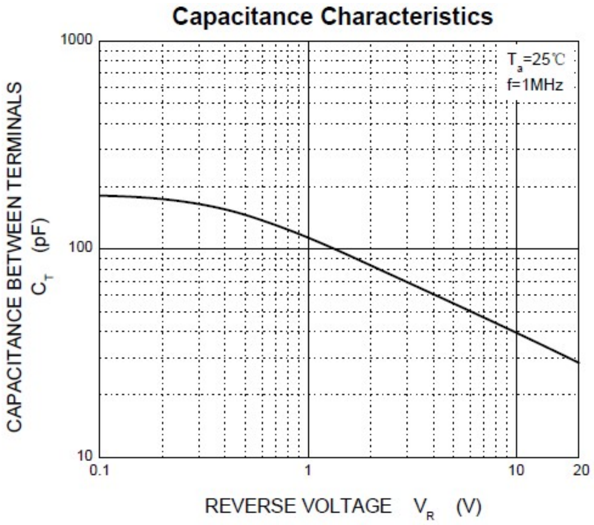
ELECTRICAL CHARACTERISTICS (Ta= 25℃)

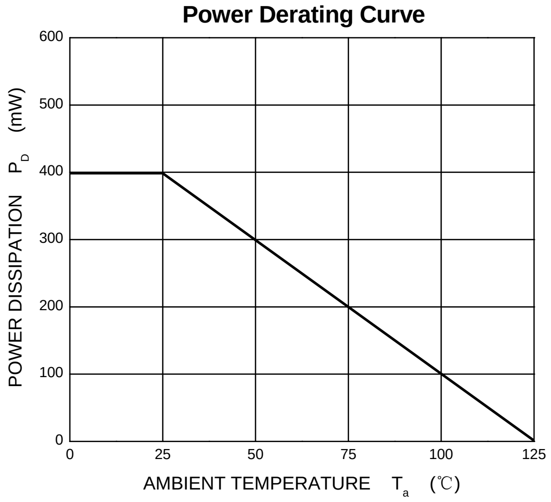
Characteristic	Symbol	Min	Typ.	Max	Unit
Forward voltage (IF = 1.0 A)	VF	-	0.54	0.56	V
Reverse current (VR=40V)	IR	-	-	30	μA

Typical Characteristics


Forward Characteristics


Reverse Characteristics


Capacitance Characteristics


Power Derating Curve